Abstract

FinFET has been a proven modification of the classical structure of MOSFETs to overcome
short channel effect. But the leakage current due to corner effect in trigate FinFET posed impediments in its way. Fin cross section shape of FinFET has considerable impact on leakage performance. In this paper trapezium and inverse trapezium PC FinFETs with various top and bottom width of fin are studied. Results show that rounding the corner and tapering the fin reduce the leakage and improves Ion/Ioff ratio.

References

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Impact of Fin Shape on Fin FET Performance


Index Terms

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Keywords

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